

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-12 (Canceled).

13. (Currently amended) A method of manufacturing a semiconductor device comprising:

~~forming a plurality of first resist patterns by~~ discharging a composition containing a photosensitizer on a first conductive layer to form a plurality of first resist patterns under reduced pressure;

exposing the plurality of first resist patterns by irradiation of light using a photomask, the light having a photosensitive wavelength region of the photosensitizer, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in each of the plurality of first resist patterns;

~~developing the irradiated plurality of first resist patterns removing one of the first portion and~~ the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns;

etching the first conductive layer by using the plurality of second resist patterns as a mask to form a plurality of gate wirings and a plurality of gate electrodes over a substrate;

removing the plurality of second resist patterns on the first conductive layer;

forming an insulating film over the plurality of gate wirings;

forming a plurality of semiconductor islands over the gate electrodes with said insulating film interposed therebetween;

~~forming a plurality of third resistant patterns by~~ discharging a composition containing a

photosensitizer on a second conductive layer to form a plurality of third resist patterns under reduced pressure;

exposing the plurality of third resist patterns by irradiation of light using a photomask, the light having a photosensitive wavelength region of the photosensitizer, wherein a third portion where the light is irradiated and a fourth portion where the light is not irradiated are formed in each of the plurality of third resist patterns;

~~developing the irradiated plurality of third resist patterns~~ removing one of the third portion and the fourth portion by developing the plurality of third resist patterns to form a plurality of fourth resist patterns;

etching the second conductive layer by using the plurality of fourth resist patterns as a mask to form a plurality of pixel electrodes arranged in a matrix form over the substrate;

removing the plurality of fourth resist patterns on the second conductive layer;

~~forming a plurality of fifth resist patterns by~~ discharging a composition containing a photosensitizer on a third conductive layer to form a plurality of fifth resist patterns under reduced pressure;

exposing the plurality of fifth resist patterns by irradiation of light using a photomask, the light having a photosensitive wavelength region of the photosensitizer, wherein a fifth portion where the light is irradiated and a sixth portion where the light is not irradiated are formed in each of the plurality of fifth resist patterns;

~~developing the irradiated plurality of fifth resist patterns~~ removing one of the fifth portion and the sixth portion by developing the plurality of fifth resist patterns to form a plurality of sixth resist patterns;

etching the third conductive layer by using the plurality of sixth resist patterns as a mask to

form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

removing the plurality of sixth resist patterns on the third conductive layer.

14. (Previously Presented) A method of manufacturing a semiconductor device according to claim 13, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

15. (Previously Presented) A method of manufacturing a semiconductor device according to claim 13, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

16. (Currently amended) A method of manufacturing a semiconductor device comprising:
~~forming a plurality of first resist patterns by~~ discharging a composition containing a photosensitizer on a first conductive layer to form a plurality of first resist patterns under reduced pressure;

exposing the plurality of first resist patterns by irradiation of light using a photomask, the light having a photosensitive wavelength region of the photosensitizer, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in each of the plurality of first resist patterns;

~~developing the irradiated plurality of first resist patterns~~ removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns;

etching the first conductive layer by using the plurality of second resist patterns as a mask to form a plurality of gate wirings and a plurality of gate electrodes over a substrate;

removing the plurality of second resist patterns on the first conductive layer;

forming an insulating film over the plurality of gate wirings;

forming a plurality of first semiconductor islands over the gate electrodes with said insulating film interposed therebetween;

forming each of a plurality of channel protective layers over each of the plurality of first semiconductor islands;

forming a plurality of second semiconductor islands over the plurality of first semiconductor islands with the plurality of channel protective layers interposed therebetween;

~~forming a plurality of third resist patterns by~~ discharging a composition containing a photosensitizer on a second conductive layer to form a plurality of third resist patterns under reduced pressure;

exposing the plurality of third resist patterns by irradiation of light using a photomask, the light having a photosensitive wavelength region of the photosensitizer, wherein a third portion where the light is irradiated and a fourth portion where the light is not irradiated are formed in each of the plurality of third resist patterns;

~~developing the irradiated plurality of third resist patterns removing one of the third portion and the fourth portion by developing the plurality of third resist patterns~~ to form a plurality of fourth resist patterns;

etching the second conductive layer by using the plurality of fourth resist patterns as a mask to form a plurality of pixel electrodes arranged in a matrix form over the substrate;

removing the plurality of fourth resist patterns on the second conductive layer;

~~forming a plurality of fifth resist patterns by~~ discharging a composition containing a photosensitizer on a third conductive layer to form a plurality of fifth resist patterns under reduced pressure;

exposing the plurality of fifth resist patterns by irradiation of light using a photomask, the light having a photosensitive wavelength region of the photosensitizer, wherein a fifth portion where the light is irradiated and a sixth portion where the light is not irradiated are formed in each of the plurality of fifth resist patterns;

~~developing the irradiated plurality of fifth resist patterns~~ removing one of the fifth portion and the sixth portion by developing the plurality of fifth resist patterns to form a plurality of sixth resist patterns;

etching the third conductive layer by using the plurality of sixth resist patterns as a mask to form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

removing the plurality of sixth resist patterns on the third conductive layer.

17. (Previously Presented) A method of manufacturing a semiconductor device according to claim 16, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

18. (Previously Presented) A method of manufacturing a semiconductor device according to claim 16, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

19. (Currently amended). A method for manufacturing a semiconductor device comprising the steps of:

~~forming a plurality of first resist patterns on an object by~~ discharging a composition on an object to form a plurality of first resist patterns under reduced pressure, the composition containing a photosensitizer;

exposing the plurality of first resist patterns with light using a photomask, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

~~developing the exposed plurality of first resist patterns~~ removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

20. (Previously presented) A method for manufacturing a semiconductor device according to claim 19, wherein viscosity of the composition is at most 100 cp.

21. (Previously presented) A method for manufacturing a semiconductor device according to claim 19, wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

22. (Previously presented) A method for manufacturing a semiconductor device according to claim 19, wherein a wavelength of light is in the range of 350 nm to 450 nm.

23. (Currently amended) A method for manufacturing a semiconductor device comprising the steps of:

~~forming a plurality of first resist patterns on an object by performing ink jetting on an object~~
to form a plurality of first resist patterns under reduced pressure, wherein each of the plurality of first resist patterns is made of a composition containing a photosensitizer;

exposing the plurality of first resist patterns with light using a photomask ,wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

~~developing the exposed plurality of first resist patterns removing one of the first portion and~~
the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

24. (Previously presented) A method for manufacturing a semiconductor device according to claim 23, wherein viscosity of the composition is at most 100 cp.

25. (Previously presented) A method for manufacturing a semiconductor device according to claim 23, wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

26. (Previously presented) A method for manufacturing a semiconductor device according to claim 23, wherein a wavelength of light is in the range of 350 nm to 450 nm.

27. (Currently amended) A method for manufacturing a semiconductor device comprising the steps of:

~~forming a plurality of first resist patterns on an object by discharging a composition on an~~
object at pressure in the range of 1×10^2 Pa to 2×10^4 Pa to form a plurality of first resist patterns,

the composition containing a photosensitizer;

exposing the plurality of first resist patterns with light using a photomask, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

~~developing the exposed plurality of first resist patterns~~ removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

28. (Previously presented) A method for manufacturing a semiconductor device according to claim 27, wherein viscosity of the composition is at most 100 cp.

29. (Previously presented) A method for manufacturing a semiconductor device according to claim 27, wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

30. (Previously presented) A method for manufacturing a semiconductor device according to claim 27, wherein a wavelength of light is in the range of 350 nm to 450 nm.

31. (Currently amended) A method for manufacturing a semiconductor device comprising the steps of:

~~forming a plurality of first resist patterns on an object by performing ink jetting at pressure in the range of 1×10^2 Pa to 2×10^4 Pa to form a plurality of first resist patterns on an object~~, wherein each of the plurality of first resist patterns is made of a composition containing a photosensitizer;

exposing the plurality of first resist patterns with light using a photomask, wherein a first

portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

developing the exposed plurality of first resist patterns removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

32. (Previously presented) A method for manufacturing a semiconductor device according to claim 31, wherein viscosity of the composition is at most 100 cp.

33. (Previously presented) A method for manufacturing a semiconductor device according to claim 31, wherein amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

34. (Previously presented) A method for manufacturing a semiconductor device according to claim 31, wherein a wavelength of light is in the range of 350 nm to 450 nm.